

Evaluation of a pulse counting type SOI pixel using synchrotron radiation X-rays

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Outline

Introduction

Evaluation of the counting type pixel

- Experimental setup
- Calibration of the discriminator
- 1-dimensional pixel array scan
- 2-dimensional pixel array scan

Summary

Introduction

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Development of the pulse counting type pixel detector for X-ray structural analysis.

- Small angle X-ray scattering experiment for functional thin films.
- X-ray diffraction experiment for functional materials such as ferroelectrics.

etc...



The Silicon-On-Insulator (SOI) technology plays a very important roll on our detector.

Introduction

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SOI detector



Double-SOI wafer (p-type substrate) Back plane : negative bias Another Si layer (middle Si) is in BOX layer

Introduction

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Requests for detectors from experiments • high spatial resolution

 \rightarrow pixel size is less than 50 μ m square

high sensitivity

 \rightarrow detecting low energy X-ray $\sim 2 \text{ keV}$

• high frame rate

 \rightarrow more than 1 kHz

Realizing by counting type pixel

Current status

X-ray test for Test-Element-Group (TEG) chip including pixel TEG.

In this talk, the experimental results of the evaluation for the counting type pixel TEG will be shown.

Evaluation of the pulse counting type pixel

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Collaborative research between IHEP and KEK.

Development of the pulse-counting-type fine pixelated X-ray detector based on Double-SOI technology.

Chip CPIXTEG3b : 50 µm square pixel 64 × 64 array



Evaluation of the pulse counting type pixel

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Experimental setup

@KEK/PF BL-14A 10 μmφ beam mode

X-ray pin-hole X-ray filter

Ionization chamber

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CPIXTEG3b chip

Experimental setup

@KEK/PF BL-14A Flat field X-ray mode



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Scattering target (Glassy carbon)

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CSR adjustment by test pulse The discriminator can be calibrated by 4-bit CSR on each pixels.

S-curve before/after CSR adjustment



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Mean distribution of S-curves



σ value became better to about 5 times. Before : 4.57 mV → After : 0.95 mV @ input pulse height

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Check by the flat field X-ray



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In the test of threshold level scan with flat field X-ray, threshold dispersion became half by CSR adjustment. Before : $26 \text{ nA} \rightarrow \text{After}$: 14 nA @threshold level

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1-dimensional pixel array scan by 10 μ m ϕ beam $E_{X-ray} = 16$ keV, $V_{HV} = -120$ V exposure time = 2 sec / 1point Threshold = ~1/4 E_{X-ray}



Scan by 5 µm step



- : Total counts of all pixels
- •••• : Counts of each pixels

Multiple count owing to charge sharing and threshold level.

→ For black points, count rate is expected to increase around boundary of pixel but no enhancement (?)

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Evaluation of pixel size and charge sharing effect

Fitting by f(x) as below

f(x) = p0 * Freq((x-p1)/p3) * (1-Freq((x-(p1+p2))/p3))



Beam size effect is not clearly contained in f(x). (implicitly included in p3)

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- p2 : size of a pixel (μ m) $\sim 45 \,\mu$ m
- **~** 45 μm
- → 5 µm smaller due to low detection efficiency in peripheral area of the pixel.
 - ? shortage of the charge collection efficiency
 - ? thickness of the depletion layer is thinner in pixel edge
- p3 : degree of the charge sharing effect @σ (μm)
 ~ 6 μm

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2-dimensional pixel array scan by 10 $\mu m \phi$ beam



Very low sensitivity in corners of a pixel. Charge was shared in 4 pixels.

Black line : boundary of the pixel

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X-ray tests for evaluating the pulse counting type pixel were done in KEK/PF BL-14A.

- Improving the degree of threshold dispersion was succeeded by discriminator calibration.
- The peripheral part of the pixel had low sensitivity.
 Especially in the corners of the pixel, sensitivity was very low because of the effect of charge sharing among 4 pixels. about 1/4 counts compared with the center area.

Outlook

The next pixel is designed to resolve charge sharing effect. It is equipped with a new charge comparing circuit which can determine a true hit pixel in multi-pixel-hit event.

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Thank you for your attention !